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PATENT FAMILY:

KOREA, REPUBLIC (KR)

Patent (No,Kind,Date): KR 2001029171 A 20010406
FLASH MEMORY AND METHOD FOR CONTROLLING THE MEMORY (English)
Patent Assignee: SAMSUNG ELECTRONICS CO LTD (KR)
Author (Inventor): KIM BEOM SU (KR)
Priority (No,Kind,Date): KR 9941835 A 19990929
Applic (No,Kind,Date): KR 9941835 A 19990929
IPC: * G11C-016/00
Language of Document: Korean

UNITED STATES OF AMERICA (US)

Patent (No,Kind,Date): US 6587915 BA 20030701
Flash memory having data blocks, spare blocks, a map block and a header
block and a method for controlling the same (English)
Patent Assignee: SAMSUNG ELECTRONICS CO LTD (KR)
Author (Inventor): KIM BUM SOO (KR)
Priority (No,Kind,Date): KR 9941835 A 19990929
Applic (No,Kind,Date): US 671176 A 20000928
National Class: * 711103000; 711206000; 711209000; 714007000;
714008000; 365185330
IPC: * G11C-016/00
Derwent WPI Acc No: ; C 02-155542
Language of Document: English

UNITED STATES OF AMERICA (US)

Legal Status (No,Type,Date,Code,Text):
US 6587915 P 19990929 US AA PRIORITY (PATENT)
KR 9941835 A 19990929
US 6587915 P 20000928 US AE APPLICATION DATA (PATENT)
(APPL. DATA (PATENT))
US 671176 A 20000928
US 6587915 P 20030701 US BA PATENT (NO PREVIOUS
PRE-GRANT PUBLICATION)